

ABSTRACT

The present invention relates to an active matrix type display providing a thin film transistor (TFT) as a switching device and the object is to provide an active matrix type display which can obtain large storage capacitor without thinning an insulating film between electrodes nor expanding an electrode to a pixel area. The active matrix type display is structured to have a plurality of gate wirings 4 formed on a glass substrate 1, a plurality of data wirings 6 formed on the glass substrate 1 substantially orthogonally to the gate wirings 4, the TFT decided by the gate wirings 4 and data wirings 6 and formed in a plurality of pixel areas arranged in a matrix shape, a pixel electrode 7 formed inside the pixel area and connected to the TFT, and a plurality of storage capacitor electrodes layers (2d, 62) forming a plurality of storage capacitors Cs1 and Cs2 between the glass substrate 1 and pixel electrode 7 via a plurality of insulating films (51,52).